

The Future of Analog IC Technology

DESCRIPTION

The MP6922A is a dual, fast-turn–off, intelligent rectifier for synchronous rectification in LLC resonant converters.

The IC drives two N-channel MOSFETs and regulates their forward voltage drop to about 30mV and turns it off before the switching current goes negative.

MP6922A has a light-load function to latch off the gate driver under light-load conditions, thus limiting the current to below 600μ A.

The MP6922A's fast turn-off enables both continuous-conduction mode and discontinuous-conduction mode. An internal reverse-current protection function ensures safe MOSFET operation under high-frequency continuous-current conditions.

MP6922A requires a minimal number of readilyavailable standard external components and is available in SOIC8E, SOIC8, and SOIC14 packages.

FEATURES

- Works with Both Standard and Logic-Level MOSFETs
- Compatible with Energy Star's 0.5W Standby Requirements
- V_{DD} Range from 8V to 24V
- 30mV V_{DS} Regulation Function ⁽¹⁾
- Fast Turn-Off Total Delay of 20ns
- Reverse-Current–Protection Function
- Maximum Switching Frequency of 300kHz
- Light Load Mode Function ⁽¹⁾ with <600µA Quiescent Current
- Supports CCM, CrCM and DCM Operation
- Available in SOIC8E, SOIC8, and SOIC14 packages
- Halogen-free

APPLICATIONS

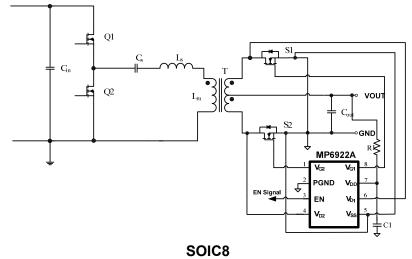
- AC-DC Adapters
- LCDs & PDP TVs
- Telecom SMPS

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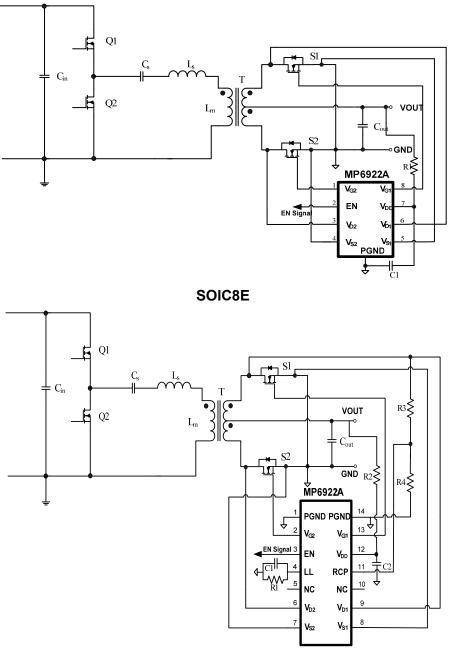
Notes:

 Related issued patent: US Patent US8,067,973; US8,400,790. CN Patent ZL201010504140.4; ZL200910059751.X. Other patents pending.

TYPICAL APPLICATION











Part Number	Package	Top Marking
MP6922AGSE*	SOIC8	MP6922A
MP6922AGN**	SOIC8E	MP6922A
MP6922AGS***	SOIC14	MP6922A

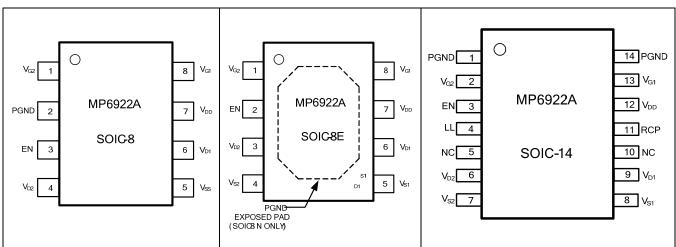
ORDERING INFORMATION

*For Tape & Reel, add suffix –Z (e.g. MP6922AGSE–Z);

**For Tape & Reel, add suffix –Z (e.g. MP6922AGN–Z);

***For Tape & Reel, add suffix -Z (e.g. MP6922AGS-Z);

PACKAGE REFERENCE



ABSOLUTE MAXIMUM RATINGS (2)

$ V_{D1} \text{ to } V_{S1}, V_{SS} \dots -0.7 \text{V to } +180 \text{V} \\ V_{D2} \text{ to } V_{S2}, V_{SS} \dots -0.7 \text{V to } +180 \text{V} \\ LL, EN \text{ to } V_{S1}, V_{S2}, V_{SS} \dots -0.3 \text{V to } +6.5 \text{V} \\ Maximum Operating Frequency} 300 \text{ kHz} \\ Continuous Power Dissipation} (T_A = +25°C) ^{(3)} \\ SOIC8 \dots 1.4 \text{W} \\ SOIC8E \dots 2.5 \text{W} \\ SOIC14 \dots 1.5 \text{W} \\ Junction Temperature} 150°C \\ Lead Temperature (Solder) \dots 260°C \\ Storage Temperature \dots -55°C \text{ to } +150°C \\ $	$\begin{array}{llllllllllllllllllllllllllllllllllll$
LL, EN to V_{S1} , V_{S2} , V_{SS} 0.3V to +6.5V Maximum Operating Frequency	V_{D1} to $V_{\text{S1}},V_{\text{SS}}$ 0.7V to +180V
Maximum Operating Frequency	V_{D2} to $V_{\text{S2}},V_{\text{SS}}$ 0.7V to +180V
Continuous Power Dissipation $(T_A = +25^{\circ}C)^{(3)}$ SOIC8	LL, EN to V_{S1} , V_{S2} , V_{SS} 0.3V to +6.5V
SOIC81.4WSOIC8E2.5WSOIC141.5WJunction Temperature150°CLead Temperature (Solder)260°C	Maximum Operating Frequency 300 kHz
SOIC81.4WSOIC8E2.5WSOIC141.5WJunction Temperature150°CLead Temperature (Solder)260°C	Continuous Power Dissipation $(T_A = +25^{\circ}C)^{(3)}$
SOIC14	
SOIC14	SOIC8E
Lead Temperature (Solder)260°C	
	Junction Temperature150°C
	Lead Temperature (Solder)260°C

Recommended Operation Conditions (4)

Thermal Resistance ⁽⁵⁾	$\boldsymbol{\theta}_{JA}$	θ _{JC}
SOIC8	90 .	45 °C/W
SOIC8E	50	10 °C/W
SOIC14	86 .	38 °C/W

Notes:

- 2) Exceeding these ratings may damage the device.
- 3) T_A=+25°C. The maximum allowable power dissipation is a function of the maximum junction temperature T_J (MAX), the junction-to-ambient thermal resistance θ_{JA} , and the ambient temperature T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P_D (MAX) = (T_J (MAX)-T_A)/ θ_{JA} . Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- 5) Measured on JESD51-7, 4-layer PCB. Without heatsink.

ELECTRICAL CHARACTERISTICS

 V_{DD} = 12V, -40°C ≤T_J≤ 125°C, unless otherwise noted.

Parameter	Symbol	Conditions		Min	Тур	Мах	Units
V _{DD} Voltage Range				8		24	V
V _{DD} UVLO Threshold		Rising		4.8	6.0	7.0	V
		Hysteresis	0.5	1	1.5	V	
Operating Current		C _{LOAD} =5nF, F _{SW} =100kHz		12	18	23	mA
Operating Current	I _{cc}	C _{LOAD} =10nF, F _{SW} =100kHz		24	27	31	mA
Shutdown Current		V _{DD} =20V, EN				600	μA
Light-Load Mode Current						600	μA
Thermal Shutdown					150		°C
Thermal Shutdown hysteresis					30		°C
Enable Shutdown Threshold		Rising		1.1	1.5	2.0	V
Enable Shuldown Threshold		Hysteresis			0.2	0.45	V
Enable UVLO Threshold		Rising		2.3	3	3.6	V
		Hysteresis			0.2	0.45	V
Internal Pull-up Current on EN					10	16	μA
CONTROL CIRCUITRY SECT	ON						
V _{S1,2} –V _{D1,2} Forward Voltage	V _{fwd}			15	30	45	mV
	т_	C _{LOAD} =5nF	-20°C≤Tյ≤125°C		150	200	ns
Turn-on delay	T _{Don}	CLOAD-5III	-40°C≤TJ<-20°C		250		115
Tum-on delay	т_	C _{LOAD} =10nF	-20°C≤Tյ≤125°C		250	300	ns
	T _{Don}		-40°C≤TJ<-20°C		350		
Input Bias Current on $V_{D1,2}$ pin		V _{D1,2} = 180V				1.5	μA
Minimum ON-Time	T _{MIN}	$C_{LOAD} = 5nF$			1		μs
Minimum OFF-Time	T _{OFF}				1.6		μs
Light-Load–Enter Delay	T _{LL-Delay}	R_{LL} =100k Ω		80	160	260	μs
Light-Load–Enter Pulse Width	T _{LL}	R_{LL} =100k Ω			2.2		μs
Light-Load Turn-On Pulse Width Hysteresis	T _{LL-H}	R_{LL} =100k Ω			0.2		μs
Light-Load–Enter OFF Period Width	T _{LL-OFF}	R_{LL} =100k Ω			50		μs
Light-Load Exit-Pulse Width Threshold (V _{D1.2} -V _{S1.2})	V _{LL-DS}			-450	-300	-140	mV
Light-load Enter-Pulse Width Threshold (V _{G1,2} -V _{S1,2})	V _{LL-GS}				1.0		V
Reverse-Current–Protection Threshold	V _{RCP}			2.5	3	3.5	V
Reverse-Current–Protection Latch Time	T _{RCP}			80	150	230	μs
GATE DRIVER SECTION	1	1			ı		1
V _{G1,2} (Low)		I _{LOAD} =1mA				0.1	V
V _{G1.2} (High)		V _{DD} >16V		13	14.5	16	V
		V _{DD} <16V			V _{DD} -2.2		
Turn-Off Threshold $(V_{S1,2}-V_{D1,2})$					-30		mV
Turn-Off Propagation Delay		$V_{D1,2} = V_{SS}$			15		ns



ELECTRICAL CHARACTERISTICS (continued)

 V_{DD} = 12V, -40°C \leq T_J \leq 125°C, unless otherwise noted.

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Turn-Off Total Delay	T _{Doff}			50	75	ns
		$V_{D1,2}$ = V_{SS} , C_{LOAD} =10nF, R_{GATE} =0 Ω		50	75	ns
Pull-Down Impedance				1	2	Ω
Pull-Down Current		3V <v<sub>G1,2<10V</v<sub>		3		А

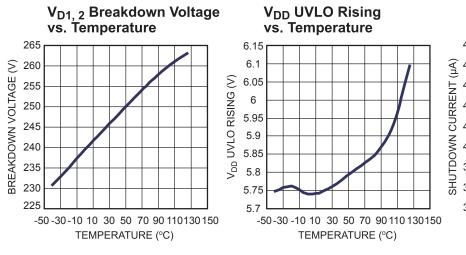


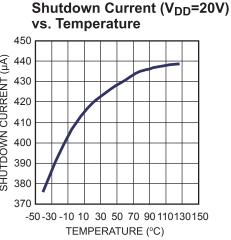
PIN FUNCTIONS

Pin # (SOIC8)	Pin # (SOIC8E)	Pin # (SOIC14)	Name	Description
1	1	2	V_{G2}	MOSFET 2 Gate Driver Output.
3	2	3	EN	Enable Pin. Enables the internal IC logic when the EN pin voltage exceeds the EN shutdown threshold; the gate driver remains latched until the EN voltage exceeds the EN UVLO threshold.
4	3	6	V_{D2}	MOSFET 2 Drain Voltage Sense
-	4	7	V_{S2}	Source pin used as reference for V _{D2} .
-	5	8	V_{S1}	Source pin used as reference for V _{D1} .
6	6	9	V_{D1}	MOSFET 1 Drain Voltage Sense.
7	7	12	V_{DD}	Supply Voltage.
8	8	13	V_{G1}	MOSFET 1 Gate Driver Output.
2	EXPOSED PAD	1,14	PGND	Power Ground. Power switch return.
-	-	5,10	NC	No Connection.
-	-	4	LL	Light-Load–Timing Set. Connect a resistor to set the light-load timing.
-	-	11	RCP	Reverse Current Protection. Internal 5V reference.
5	-	-	V_{SS}	Common Source. Used as reference for both channels.

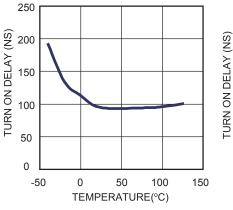


TYPICAL CHARACTERISTICS

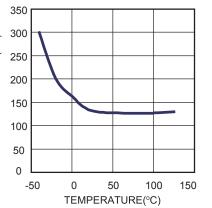




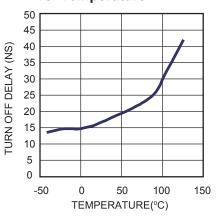
Turn On Delay (Cload=5nF) vs. Temperature

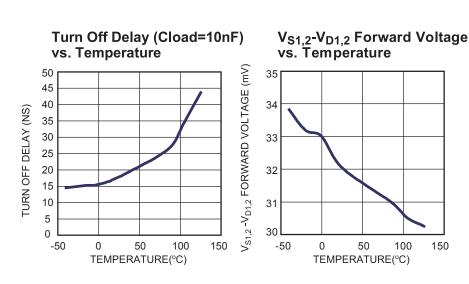


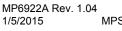
Turn On Delay (Cload=10nF) vs. Temperature



Turn Off Delay (Cload=5nF) vs. Temperature



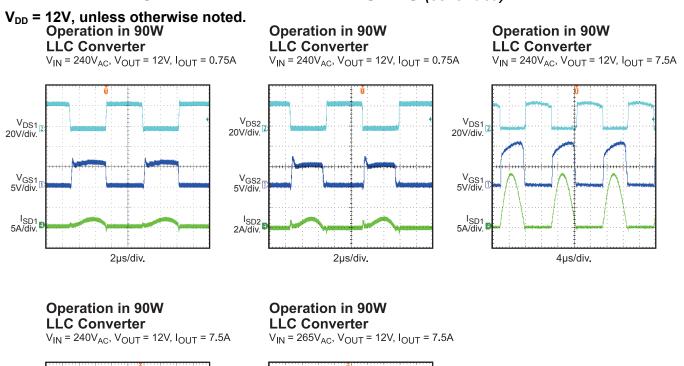


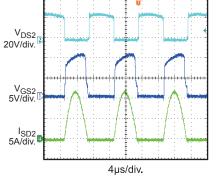


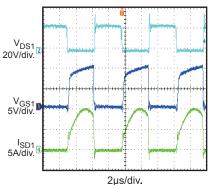
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TYPICAL PERFORMANCE CHARACTERISTICS (continued)









BLOCK DIAGRAM

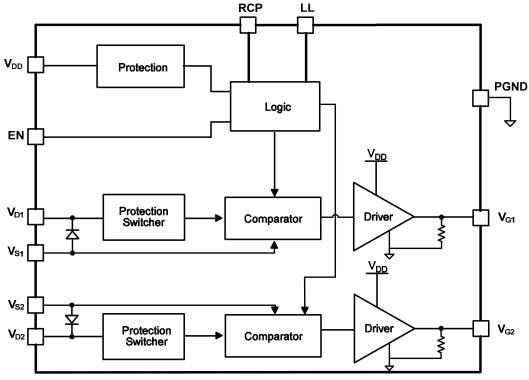


Figure 1: Functional Block Diagram



OPERATION

The MP6922A operates in discontinuousconduction mode (DCM), continuous-conduction mode (CCM), and critical conduction mode (CrCM) condition. Operating in either DCM or CrCM, the control circuitry controls the gate in forward mode; it turns the gate off when the MOSFET current is low. In CCM, the control circuitry turns off the gate during very fast transients.

Blanking

The control circuitry contains a blanking function that ensure that when the MOSFET turns ON/OFF, the MOSFET remains in that state for ~1µs, which determines the minimum ON-time. During the turn-on blanking period, the turn-off threshold is not totally blanked, but changes to ~+100mV (instead of +30mV). This ensures that the part can always turn OFF even during the turn-on blanking period (albeit slower, so avoid setting the synchronous period to less than 1µs at CCM condition in the LLC converter to eliminate shoot-through).

VD Clamp

The MP6922A uses a high-voltage JFET at its input because $V_{D1,2}$ can go as high as 180V. Connect a small resistor between the $V_{D1,2}$ pin and the external MOSFET drain to avoid excessive currents when V_G goes below -0.7V.

Under-Voltage Lockout (UVLO)

When V_{DD} goes below the UVLO threshold, the part enters sleep mode and a $10k\Omega$ resistor pulls down $V_G.$

Enable Pin

If EN is pulled low, the part enters sleep mode.

Thermal Shutdown

If the junction temperature of the IC exceeds 150° C, V_G is pulled low and the part stops switching. The part resumes normal operation after the junction temperature has dropped to 120° C.

Turn-On Phase

 V_{DS} (V_D – V_{SS}) goes negative (<-500mV) when the switch current flows through the MOSFET's body diode. If V_{DS} is much lower than the turn-on threshold of the control circuitry (-30mV), then

the MOSFET turns on after about 200ns turn-on delay (Figure 2).

Triggering the turn-on threshold (-30mV) causes the circuit to add a blanking time (minimum ontime 1 μ s), during which the turn-off threshold changes from +30V to +100mV. This blanking time avoids erroneous triggering caused by ringing on the synchronous power switch.

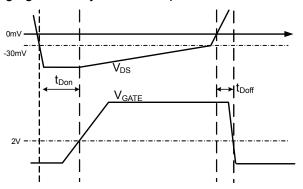


Figure 2: Turn-On and Turn-Off delay

Conducting Phase

When the MOSFET turns ON, V_{DS} ($-I_{SD} \times R_{DS(ON)}$) rise relative to the switch current (I_{SD}) drop. When V_{DS} rises above the turn-on threshold (-30mV), the control circuitry stops pulling up the gate driver and the MOSFET driver voltage drops, which increases the MOSFET's $R_{DS(ON)}$. This adjusts V_{DS} ($-I_{SD} \times R_{DS(ON)}$) to around -30mV even when the switch current I_{SD} is fairly small, and can prevent the internal driver from triggering until the current through the MOSFET has dropped to near zero.

Turn-Off Phase

When V_{DS} rises to trigger the turn-off threshold (30mV), the control circuitry pulls down the driver switch voltage after a 20ns turn-off delay (shown in Figure 2). Similarly, a 1.6µs blanking time occurs after the switch turns off, during which the MOSFET does not turn on to avoid erroneous triggering.

Figure 3 shows the MP6922A operating under a heavy-load. The high current initially saturates the driver voltage. After V_{DS} goes above -30mV, the driver voltage decreases to adjust the V_{DS} to around -30mV.

Figure 4 shows the MP6922A operating at lightload. The low current prevents the driver voltage from saturating but decreases when the synchronous power switch turns on and adjusts V_{DS} .

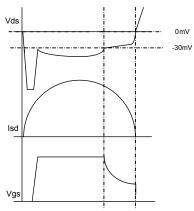


Figure 3: Synchronous Rectification Operation at Heavy Load

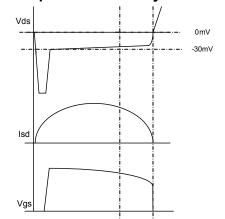


Figure 4: Synchronous Rectification Operation at Light Load

Light-Load Latch-Off Function

The gate driver of MP6922A is latched to limit driver losses under light-load condition to improve light-load efficiency.

Normal Operation Latch Off

When the MOSFET's switching-cycle conducting period falls below $2.2\mu s$ (τ_{LL}), the MP6922A enters light-load mode and latches off the MOSFET after a 160 μs delay (light-load-enter delay, $\tau_{LL-Delay}$)

After entering light-load mode, the MP6922A monitors the MOSFET's body diode conducting period by sensing V_{DS} (when V_{DS} exceeds – 300mV (V_{LL-DS}), MP6922A treats the the MOSFET's body-diode conducting period as finished). If the MOSFET's body diode conducting period exceeds 2.4µs ($T_{LL}+T_{LL-H}$), light-load mode ends and the MOSFET unlatches to restart the synchronous rectification.

For the SOIC14 package. the MP6922A has an LL pin that allows τ_{LL} to be adjusted by an external resistor:

$$\tau_{LL} = 2.2 \mu s \cdot \frac{R_{LL}}{100 k\Omega}$$

Latch Off during Burst Operation

The IC also monitors the synchronous MOSFET OFF period. If the OFF period exceeds the light-load–enter OFF period width (τ_{LL-OFF}), the MP6922A enters light-load mode and latches off the gate driver.

The gate driver is unlatched when the drain-source voltage of the synchronous MOSFET V_{DS} drops below –30mV.

Reverse Current–Protection Function

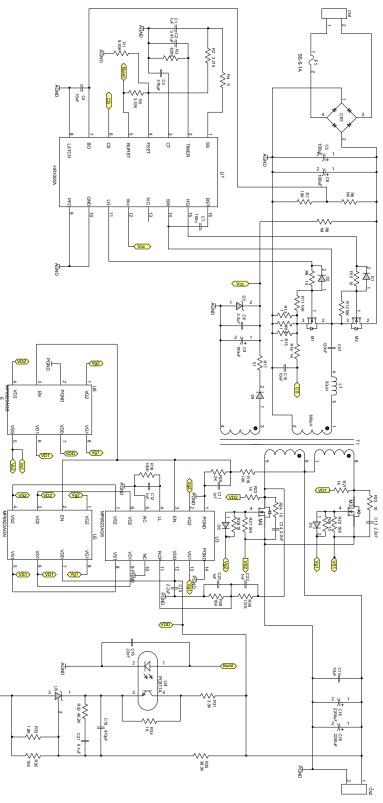
When the LLC system operates in CCM at a very high frequency, the synchronous current may reverse before the IC turns off the gate driver, which can lead to shoot-through (in centertapped outputs with full-wave rectification topologies). The MP6922A has a protection function to latch off the gate driver when the current reverses before the driver signal is pulled low.

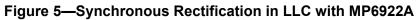
When the synchronous current reverses, the high spike can be observed between the MOSFET's drain/source. The MP6922A monitors the voltage through the RCP pin using a voltage divider. When the voltage of RCP pin exceeds V_{RCP} , MP6922A latches the driver signal of both channels for ~150µs (T_{RCP}) to protect the synchronous MOSFET. At the end of T_{RCP} , MP6922A restarts the synchronous rectification.



TYPICAL APPLICATION CIRCUIT

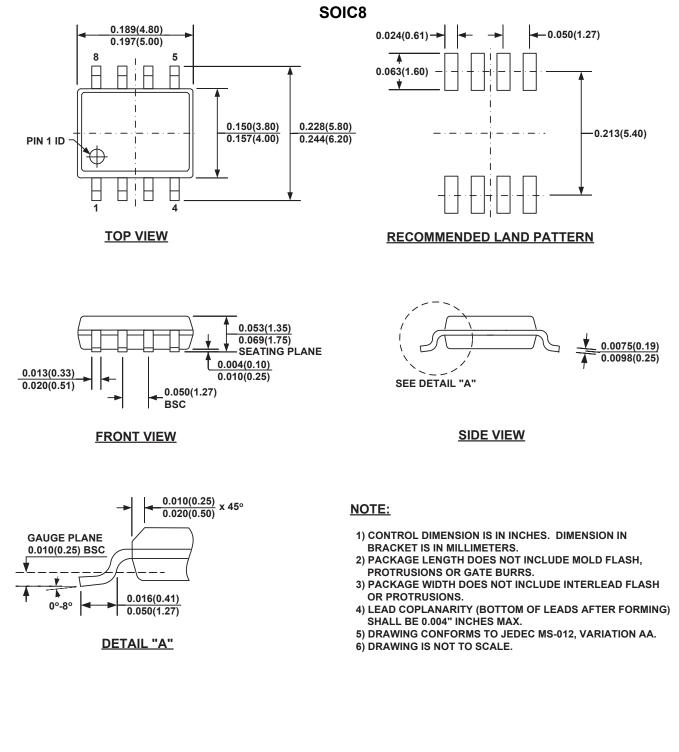
PGND







PACKAGE INFORMATION





SOIC8E (EXPOSED PAD)

